

ABSTRACT

A method is disclosed for manufacturing bit line contact structures of semiconductor memories. The manufacturing method comprises the steps of providing a semiconductor substrate, forming a plurality of gates on the surface of the substrate, applying a first insulating layer to cover the surface of the substrate and the gates, selectively forming a plurality of gate contact windows at the locations of the gates, selectively forming bit line contact windows in the first insulating layer, the bit line contact windows contacting the substrate, and filling the gate contact windows and the bit line contact windows with a conductive layer.